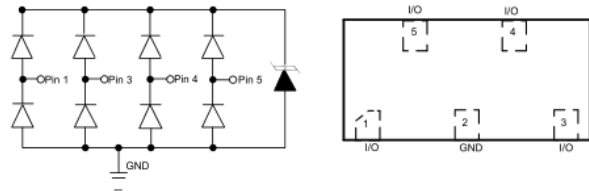
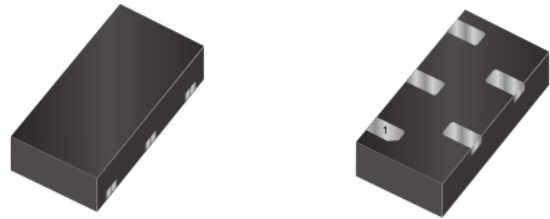


Features

- ◆ 30Watts peak pulse power ($t_p = 8/20\mu s$)
- ◆ DFN 2010 Package
- ◆ Protect up to 4-lines
- ◆ Solid-state silicon-avalanche technology
- ◆ Low clamping voltage
- ◆ Low leakage current
- ◆ Low capacitance (0.2pF typical I/O to I/O)
- ◆ ESD Protection for high-speed data lines to:
 - IEC 61000-4-2 $\pm 8kV$ contact $\pm 15kV$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 3A (8/20 μs)



Applications

- ◆ USB 3.0/3.1, Type C
- ◆ HDMI 1.4/2.0, Display Port 1.3
- ◆ Unified Display interface
- ◆ Digital visual interface
- ◆ Microcontroller Input Protection

Mechanical data

- ◆ Case: DFN2010 (plastic package). Lead free; RoHS compliant
- ◆ Molding Compound Flammability Rating: UL 94 V-0
- ◆ Terminals: High temperature soldering guaranteed: 260 °C/10 sec. at terminals

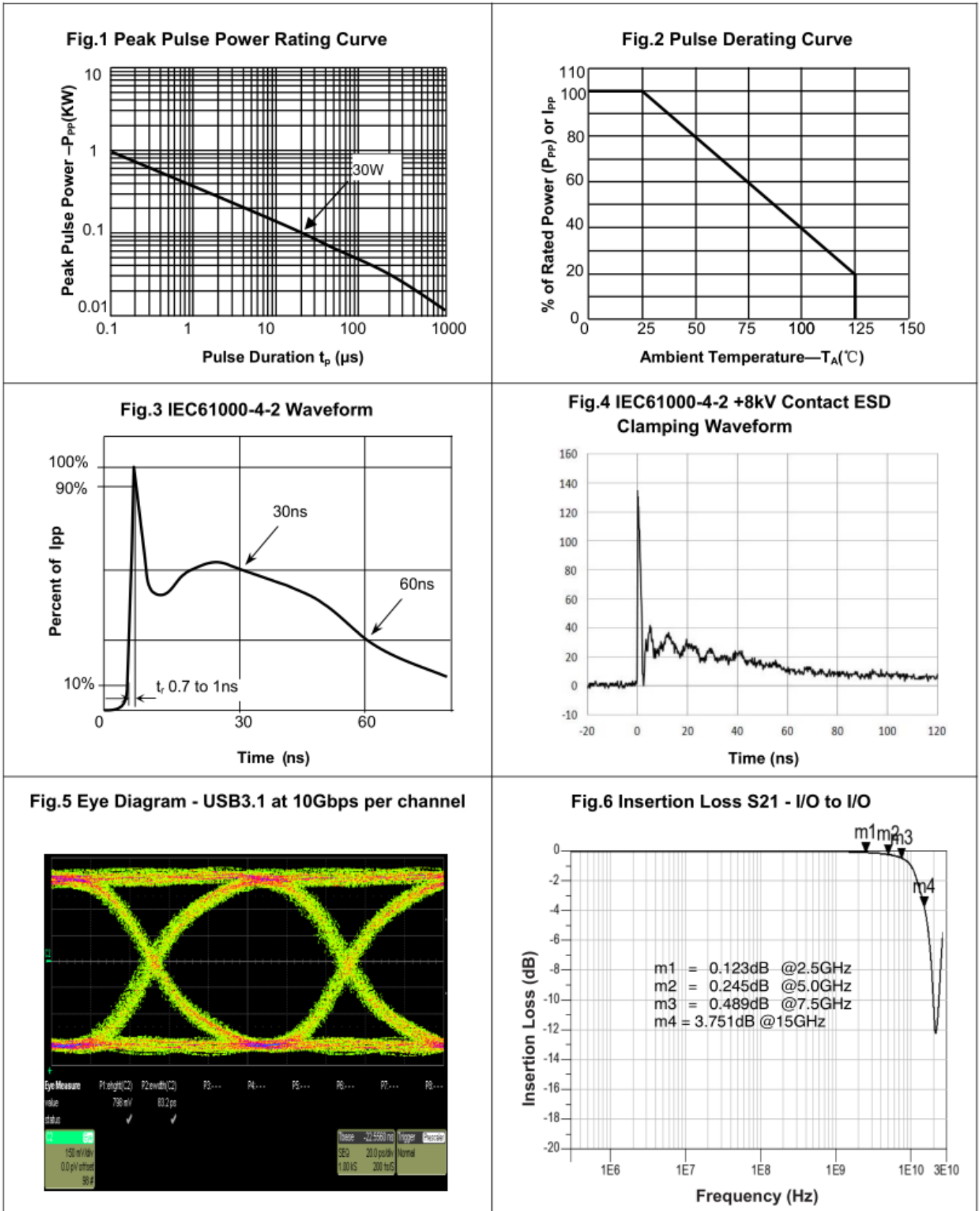
Absolute Maximum Ratings (Ratings at 25 °C, ambient temperature unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_p=8/20\mu s$)	P_{PP}	30	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	8/15	kV
Peak Pulse Current ($t_p = 8/20\mu s$)	I_{PP}	3	A
Junction Temperature	T_J	-55 to +125	°C
Storage temperature	T_{STG}	-55 to +150	°C

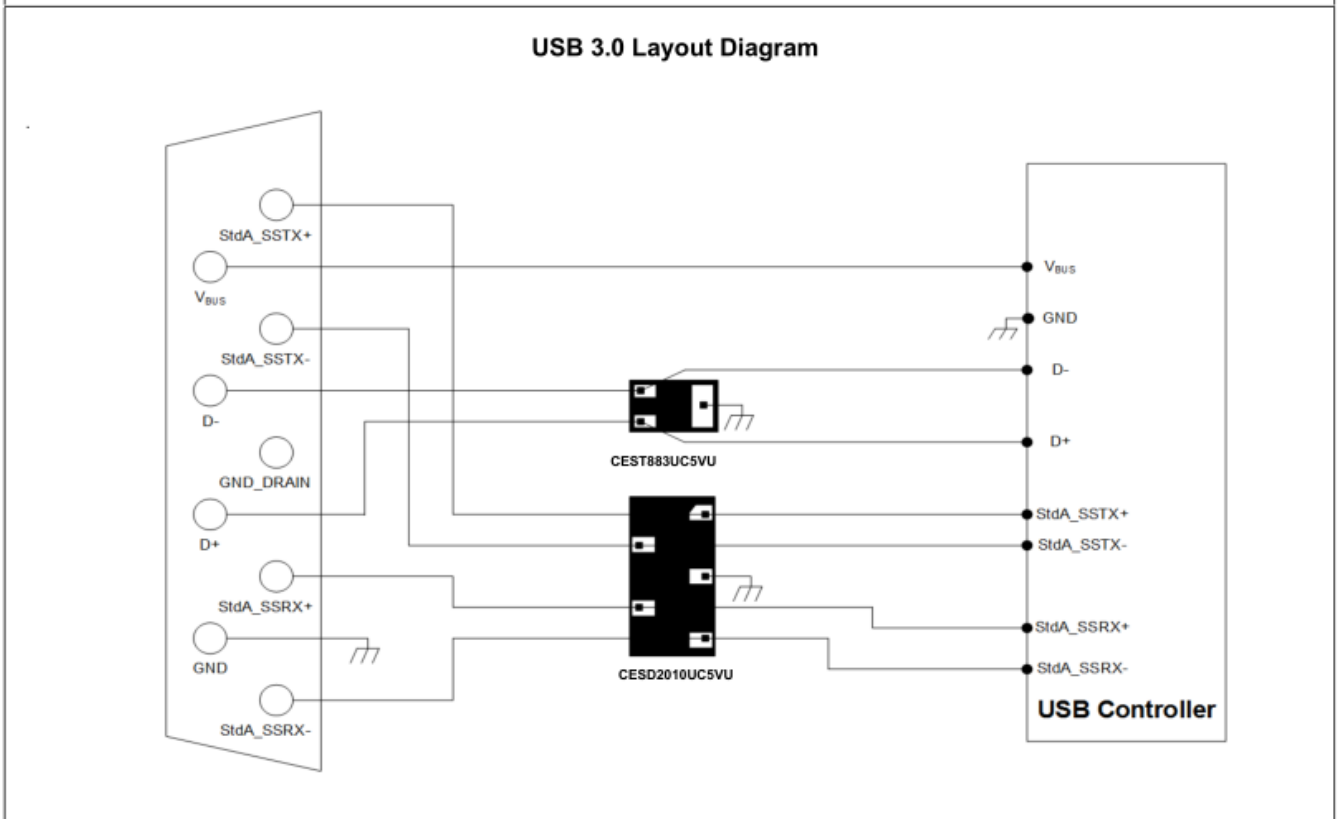
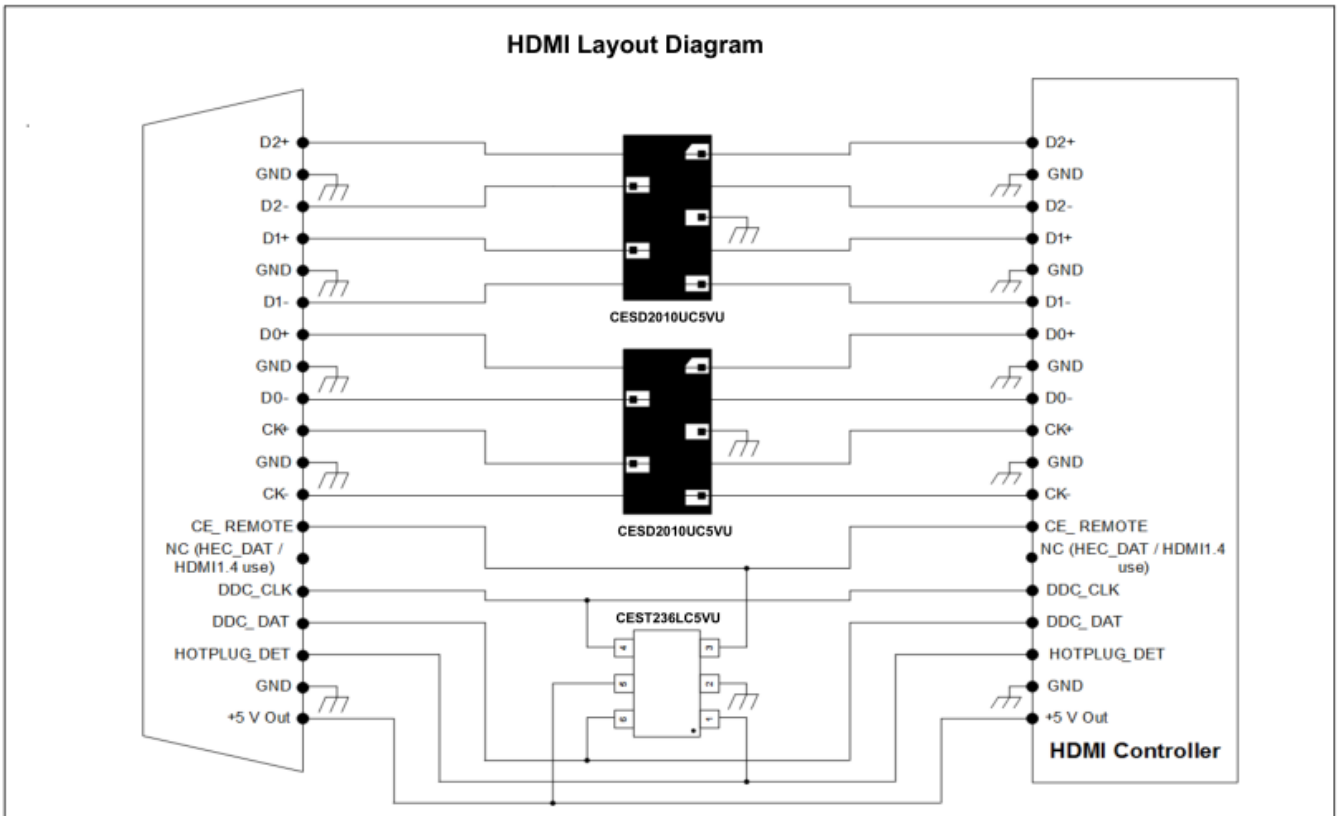
Electrical Characteristics ($T_A = 25$ °C unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}				5	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6	7.2	9.5	V
Reverse Leakage Current	I_R	$V_R=5V$		0.1	0.5	μA
Clamping Voltage(SURGE)	V_C	$I_{pp}=3A, T_p=8/20\mu s$			10	V
Junction Capacitance	C_J	$V_R=0V, f=1MHz, I/O$ to I/O		0.2		pF
	C_J	$V_R=0V, f=1MHz, I/O$ to GND		0.2		pF

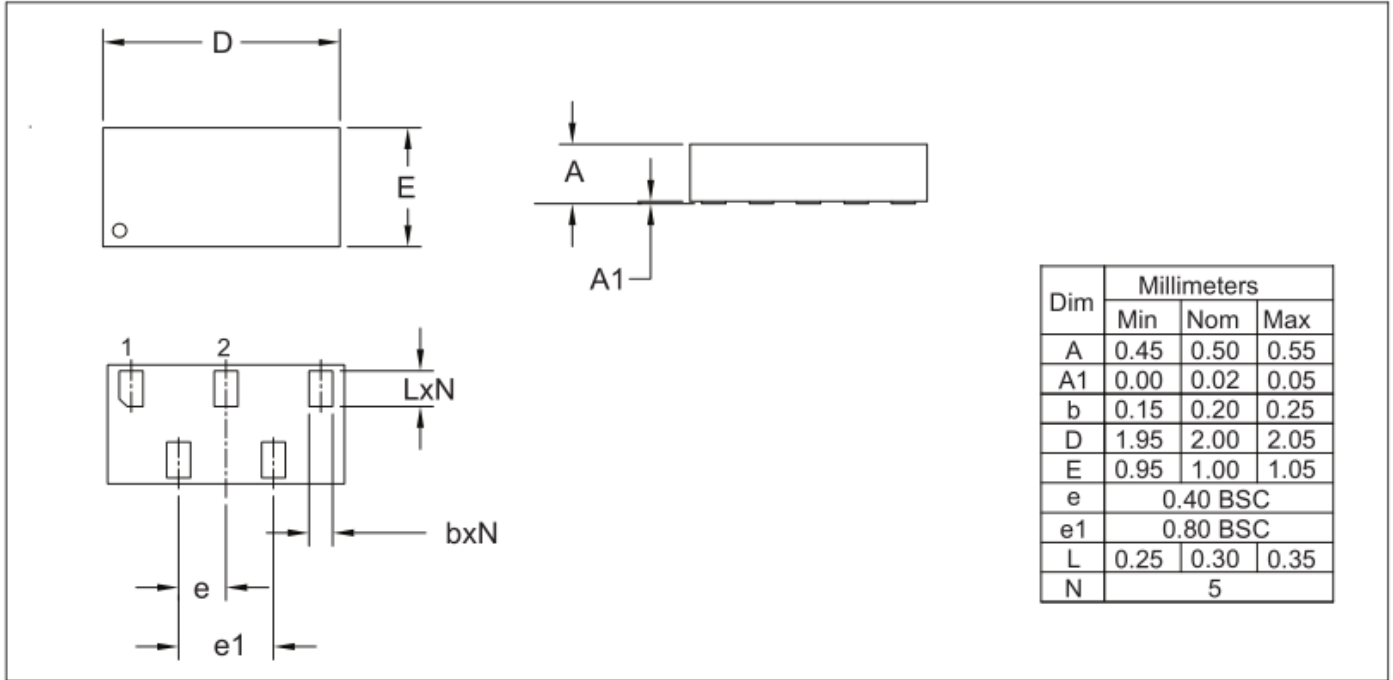
Typical Characteristics (T_{amb} = 25°C unless otherwise specified)



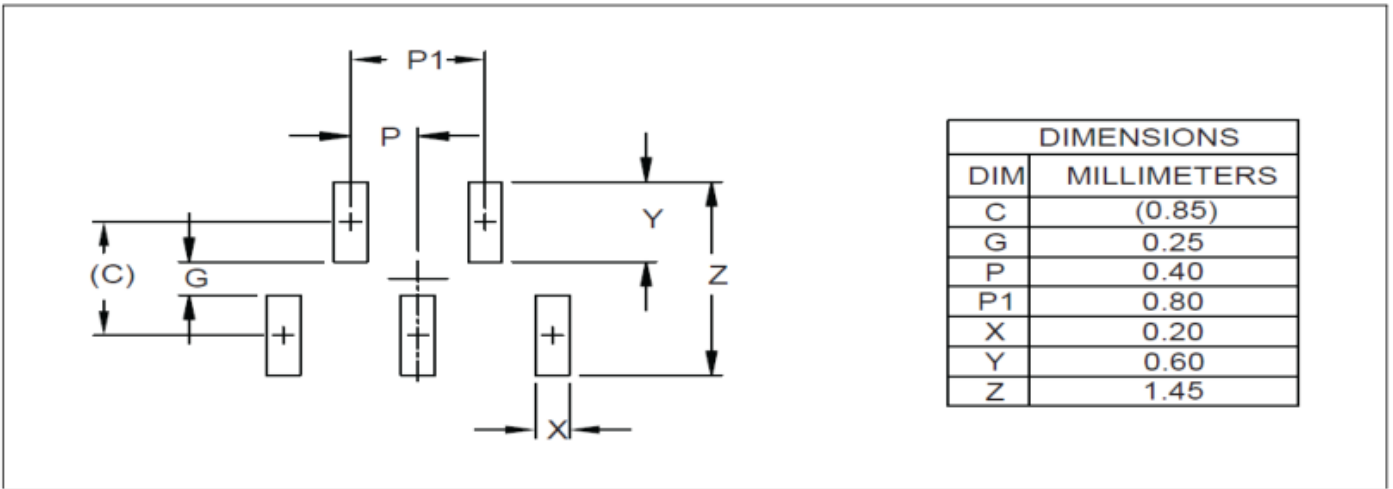
Layout Diagrams



Package Dimensions



PAD Dimensions



Ordering information

Order code	Marking	Package	Packaging option	Base quantity	Packaging specification
CESD2010UC5VU	M534	DFN2010	Tape and reel	3000pcs / reel	EIA STD RS-481